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Sheet 1 of 1

Complete if Known	
Application Number	10/091,338
Filing Date	March 6, 2002
First Named Inventor	Toru MITSUKI et al.
Group Art Unit	2824
Examiner Name	Bradley Smith
Attorney Docket Number	0756-2448

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.1	U.S. Patent Documents Number	Kind Code1 (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.1	Foreign Patent Document Office3	Number4	Kind Code4 (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T5
BKS		JP	07-162004			06/23/1995		AB
		WO	93-10555			05/27/1993		AB
		JP	04-035021			02/05/1992		AB
↓		JP	04-286336			10/12/1992		AB

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T5
BKS		H. ~~Kuseki et al.~~, *Recent Progress of Low Temperature Poly-Si Technology*, Electronic Display Forum, Pages 4-31 to 4-38 and English Translation, Pages 1-21, April ~~15~~ 14, 1999.	
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BKS Tsutsu

Examiner Signature		Date Considered	6/15/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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